

TO-126 Plastic-Encapsulate Transistors

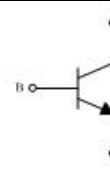
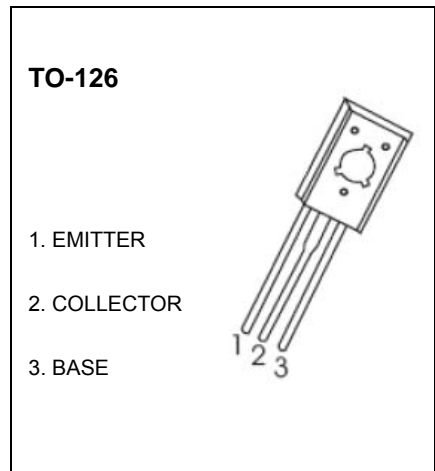
C 2611 TRANSISTOR (NPN)

FEATURE

power switching applications

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector -Base Voltage	600	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current -Continuous	0.2	A
P _C	Collector Power Dissipation	1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	600			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} = 600V, I _E =0			100	μA
Collector cut-off current	I _{CEO}	V _{CE} = 400V, I _B =0			200	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			100	μA
DC current gain	h _{FE(1)}	V _{CE} =20V, I _C =20mA	10		40	
	h _{FE(2)}	V _{CE} =10V, I _C = 0.25mA	5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 50mA, I _B = 10mA			0.5	V
		I _C = 100mA, I _B = 20mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 50mA, I _B =10mA			1.2	V
Transition frequency	f _T	V _{CE} =20V, I _C =20mA f = 1MHz	8			MHz
Fall time	t _S	I _C =50mA, I _{B1} =-I _{B2} =5mA, V _{CC} =45V			0.3	μs
Storage time	t _f				1.5	μs

CLASSIFICATION OF h_{FE(1)}

Rank						
Range	10-15	15-20	20-25	25-30	30-35	35-40